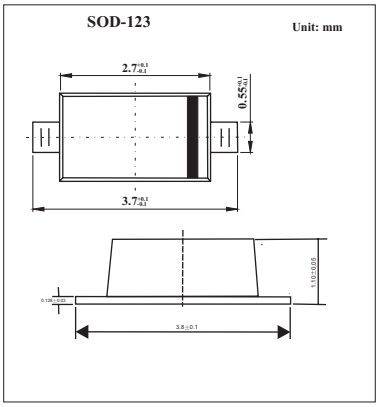
Schottky Barrier Diode
RB160M-30



■ Features

- Small power mold type.
- Low IR
- High reliability

■ Absolute Maximum Ratings Ta = 25℃

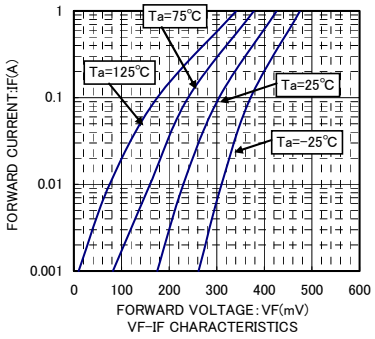
Parameter	Symbol	Rating	Unit
Reverse voltage	V_{RM}	30	V
reverse voltage	V_R	30	V
Forward current surge peak	Io	1	A
Average rectified forward current	I_{FSM}	30	A
operating junction temperature	T_j	125	℃
storage temperature	T_{stg}	-40 to +150	℃

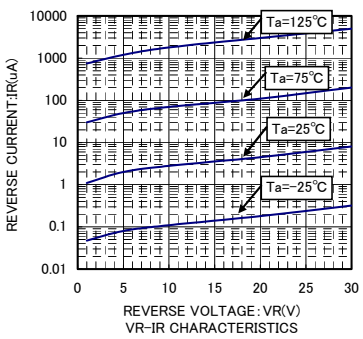
■ Electrical Characteristics Ta = 25℃

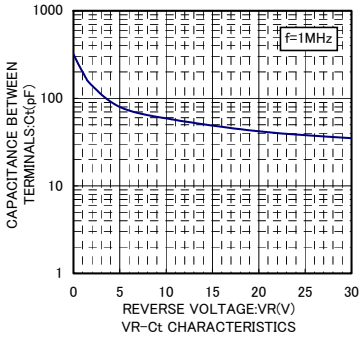
Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Forward voltage	V_{F1}	I_F=0.5A		0.39	0.46	V
	V_{F2}	I_F=1.0A		0.43	0.48	V
Reverse current	I_{R1}	V_R=15V		3.0	20	μA
	I_{R2}	V_R=30V		9.0	50	μA

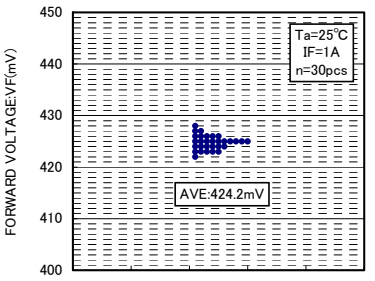
RB160M-30

●Electrical characteristic curves (Ta=25°C)

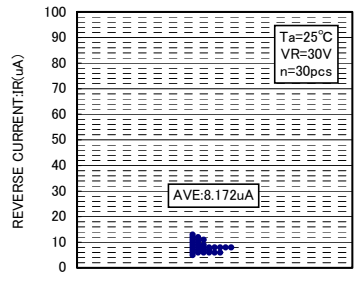




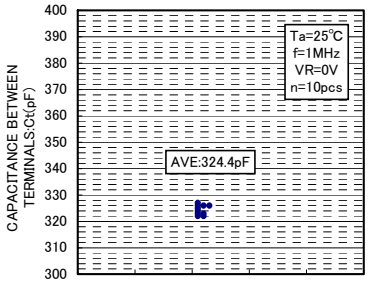




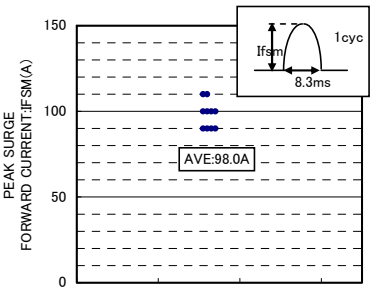
VF DISPERSION MAP



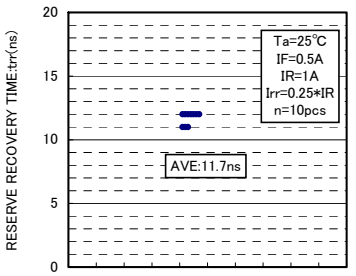
IR DISPERSION MAP



Ct DISPERSION MAP



IFSM DISRESION MAP



trr DISPERSION MAP